

2SD718

Silicon NPN Transistors

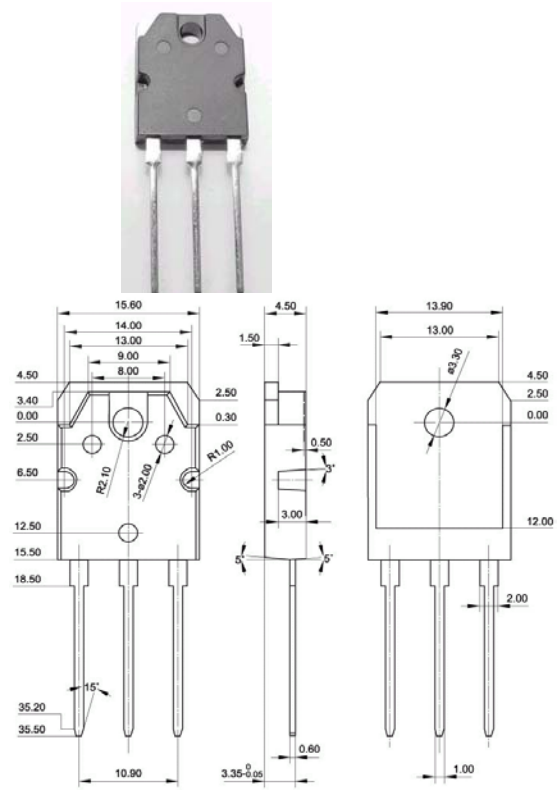
B C E

Features:

- With TO-3P(I) package
- Complement to type 2SB688

◆ Absolute Maximum Ratings Tc=25 °C

SYMBOL	PARAMETER	RATING	UNIT
V _{CB0}	Collector to base voltage	120	V
V _{CEO}	Collector to emitter voltage	120	V
V _{CER}	Emitter to base voltage		
V _{EB}	Emitter to base voltage	5	V
I _B	Base Current		
I _C	Collector current-Continuous	8	A
P _D	Total Power Dissipation@TC=25 °C	80	W
T _j	Junction temperature	150	°C
T _{stg}	Storage temperature	-65~150	°C



TO-3P(I)

◆ Electrical Characteristics Tc=25 °C

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =50mA; I _B =0	120		V
V _{CB0}	Collector-Base Voltage				
I _{CEO}	Collector Cutoff Current	V _{CE} =120V; I _B =0		0.1	mA
I _{CB0}	Collector Cutoff Current	V _{CB} =120V; I _E =0		0.1	mA
I _{EBO}	Emitter Cutoff Current				
V _{EBO}	Emitter Cutoff Current	I _E =10mA; I _C =0	5		V
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =5A; I _B =0.5A		2.5	V
V _{CE(sat-2)}	Collector-emitter saturation voltages				
V _{CE(sat-3)}	Collector-emitter saturation voltages				
V _{CE(sat-4)}	Collector-emitter saturation voltages				
h _{FE-1}	Forward current transfer ratio	I _C =1A; V _{CE} =5V	55	160	
h _{FE-2}	Forward current transfer ratio				
V _{BE(sat)}	Base-emitter saturation voltages	I _C =5A; I _B =0.5A		3.0	V
f _T	Current Gain-Bandwidth Product				

Note Hfe Classification

R	O
55-110	80-160